



Docket No.: 042390.P11362

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Brian S. Doyle

Application No.: 09/895,579

Filed: June 29, 2001

For: CREATION OF HIGH MOBILITY
CHANNELS IN THIN-BODY SOI
DEVICES

Examiner: David Nhu

Art Group: 2818

10/24/2002 GSTANLEY 00000001 022666 09895579

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84.00 CH
234.00 CH

AMENDMENT AND RESPONSE TO THE OFFICE ACTION

Box Non-Fee Amendment
Assistant Commissioner for Patents
Washington, DC 20231-9998

Sir:

In response to the outstanding Office Action mailed May 1, 2002, please amend the above-identified Application as follows:

IN THE SPECIFICATION

Please replace the heading on page 1, line 6, with the following rewritten heading:

-- DESCRIPTION OF THE RELATED ART --

Please replace the sentence beginning on page 3, line 17, with the following rewritten sentence:

-- The relaxed SiGe layer has the thickness in the range of approximately from 0.1 μ m to 3.0 μ m.--

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TECHNICAL STAFF 2800

RECEIVED

TMM/bh